

Silicon NPN Power Transistors

2SC1316

DESCRIPTION

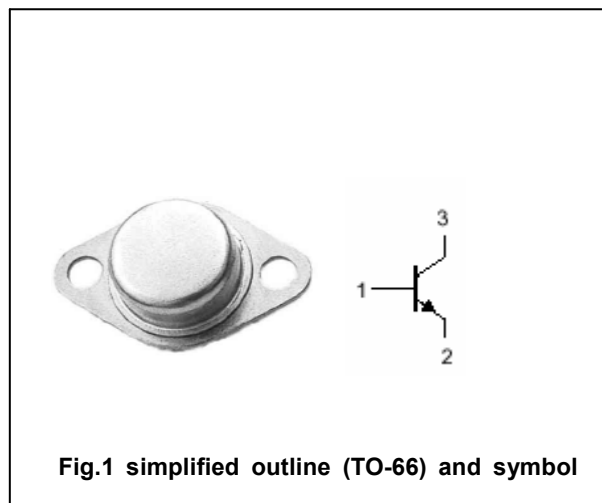
- With TO-66 package
- High breakdown voltage

APPLICATIONS

- Suitable for switching power supplies in TV sets

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings (Ta=25℃)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	750	V
V_{CEO}	Collector-emitter voltage	Open base	750	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		2	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	23	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	750			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A ; I _B =0.2A			3.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1A ; I _B =0.2A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =750V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =3V	4		14	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		8.5		MHz

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PACKAGE OUTLINE

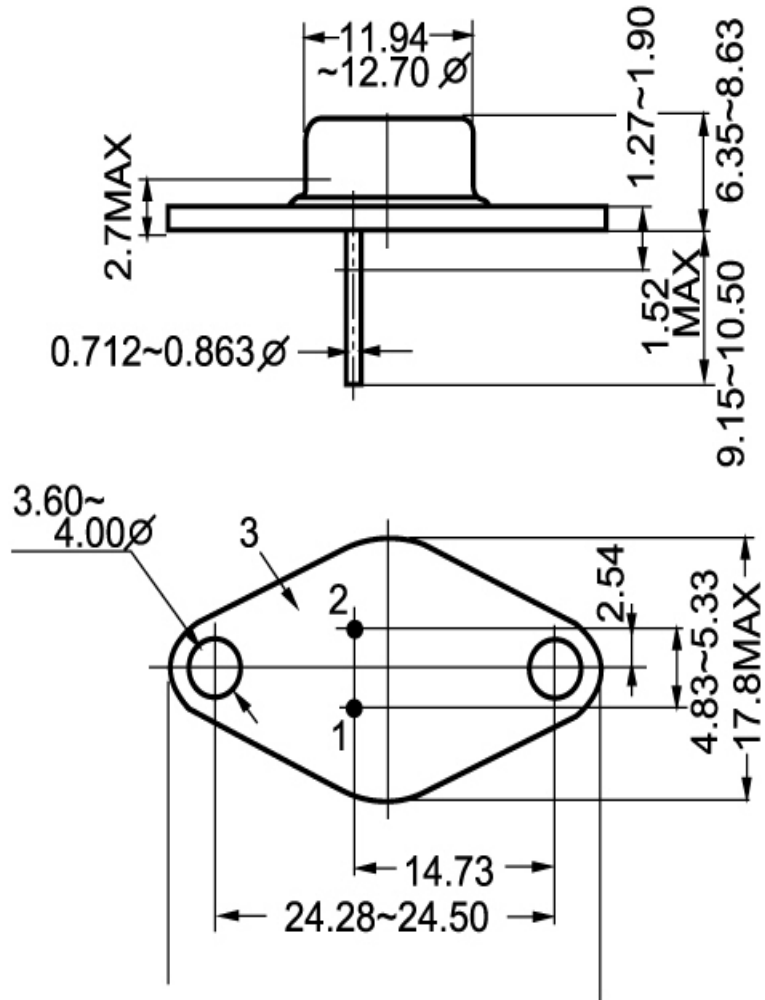


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)